

Appl. No. 10/510,591
Amdt. dated June 21, 2005
Reply to Office Action of June 14, 2005

Amendments to the Claims

1. (*Previously Presented*) A semiconductor device comprising a carrier with a first and a second side situated opposite to each other, which carrier has a first electroconductive layer on the first side, which electroconductive layer is patterned in accordance with a desired pattern, thereby defining a number of mutually isolated connection conductors,

on which first side of the carrier a semiconductor element is present, which semiconductor element is provided with connection regions that are electroconductively connected via connection means with the connection conductors of the carrier, which semiconductor element is encapsulated in a passivating envelope that extends as far as the carrier,

on which second side, contact surfaces are defined in the connection conductors for placement on a substrate,

characterized in that the envelope is mechanically anchored in the connection conductors, for which purpose the connection conductors are provided with side faces having recesses.

2. (*Original*) A semiconductor device as claimed in claim 1, characterized in that, in addition to the first layer, the carrier comprises a second layer and a third layer, the second layer comprising a material that can be etched in an etchant that leaves the first and the third layer substantially in tact.

3. (*Previously Presented*) A semiconductor device as claimed in claim 1, characterized in that the apertures extend as far as the second side of the carrier.

4. (*Original*) A semiconductor device as claimed in claim 1, characterized in that the connection means are bumps, which bumps are also used to attach the semiconductor element onto the carrier.

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5. (*Original*) A semiconductor device as claimed in claim 2, characterized in that the first and the third layer contain copper, and the second layer contains a material selected from the group composed of Al and Ni-Fe.

6. (*Previously Presented*) A semiconductor device as claimed in claim 1, characterized in that the carrier comprises a number of electrically insulating and conductive layers, at least one passive component being embedded in said layers.

Claims 7-12 (*Cancelled*)